

Index

a

active metal conductive filament
 mechanism 138
 Ag/CH₃NH₃PbI_(3-x)Cl_x/FTO structure
 150–151
 Ag₅In₅Sb₆₀Te₃₀ 127
 AgInSbTe (AIST)-based chalcogenide
 material 136
 Ag nanoclusters 97, 190
 Ag/PEDOT:PSS/Ta memristor 150, 151
 Ag/SiO₂/Pt device 9
 Al/CH₃NH₃PbBr₃/BCCP/ITO 154
 all-spin artificial neural network
 (ASANN) 61–62
 all-spin spiking neural network (ASSNN)
 62
 analog-like synaptic device 52–54
 analog-to-digital converters (ADCs) 179
 animals' sensorimotor system 226
 anion migration related filaments 8,
 11–14
 ANN computing 36–39
 application-specific integrated circuits
 (ASICs) 174
 artificial auditory device 113–114
 artificial intelligence (AI) 17, 91, 125,
 158, 173
 artificial intelligence of things (AIoT)
 125
 artificial neural device 57–61
 artificial neural networks (ANNs) 7, 51,
 91, 125

artificial neurons based on TS effects
 136–139
 artificial perception 221
 artificial perceptual system for pattern
 recognition 226
 artificial sensory neuron 221–225
 artificial synapses based on MS behaviors
 129–136
 artificial tactile device 109–112
 artificial tactile neuron 222
 artificial vision device 112–113
 artificial visualization systems 166–167
 as-fabricated heterosynaptic device 98
 associative memory based injection
 locking 73–74
 Atkinson-Shiffrin multi-store memory
 model 94
 atomic layer deposition (ALD) 2
 Au/Li_xMoS₂/Au memristor 96, 97

b

backpropagation-STDP (BP-STDP) 189
 Bienenstock–Cooper–Munro (BCM) 23,
 24, 26
 big data 18
 bi-layered HfO₂/TiO_x cognitive memristor
 93, 94
 binarized neural networks (BNNs) 185
 binary magnetic tunnel junction 48–49
 biological neural networks (BioNNs) 27,
 173
 biological neurons 28
 biological synapses 19

- bioNNs 174
 - biophysical memristive neurons 34–36
 - bioplausible memristive neurons 31–34
 - biorealistic memristive synapses 22
 - bio-voltage diffusive memristor 190
 - bit slicing scheme 185
 - bottom electrode (BE) 11, 12, 34, 93, 131, 150, 154
 - Braindrop 176
 - brain-inspired multi-functional
 - perception learning system 95
 - brain-inspired neuromorphic computing 125
 - brain-like neuromorphic devices 91
- c**
- calmodulin-dependent kinase II 96
 - capacitively coupled neuro-transistors 114
 - 2048-cell TiN/TaO_x/HfO₂/TiN memristor array 183
 - chalcogenide materials
 - artificial neurons based on TS effects 136–139
 - artificial synapses based on MS behaviors 129–136
 - hardware neural networks 139–143
 - ovonic memory switching (OMS) 126–129
 - ovonic threshold switching (OTS) 126–129
 - charge-trapping-based memristors 155–157
 - chemical-biosensors 101–102
 - chemical vapor deposition (CVD) 3
 - CMOS-based in-situ nonlinear activation (ISNA) modules 195
 - CMOS-based neuromorphic computing 174–176
 - C₆₀ nanoparticles 158
 - C₃N₄ nanodots 112
 - complementary
 - metal-oxide-semiconductor (CMOS) 39, 72, 150
 - computing-in-memory (CIM) hardware 174
 - conditioned stimulus (CS) 108, 113
 - conductive filaments (CFs) 8, 41, 97
 - confined-type phase-change memory 130
 - convolutional neural networks (CNNs) 37, 125, 139, 173
 - CsPbBr₃ QDs 164, 165
- d**
- deep belief networks (DBNs) 173
 - deep neural networks (DNNs) 173
 - Delta rule 37, 38
 - dendrite neuron and dendritic algorithm 106–109
 - dendritic computing 196–202, 205
 - device-to-application simulation system 178
 - digital-analog converters (DACs) 179
 - 2,7-dioctyl[1]benzothieno[3,2-*b*][1]benzothiophene (C8-BTBT) 164
 - DNNs based on synaptic devices
 - architecture and algorithm optimization 185
 - array demonstrations 179–182
 - chip and system implementations 183–185
 - device performance requirements 178–179
 - dopamine 102
 - dual-gate IZO-based EDL transistor 104
 - dual-organic-transistor-based
 - tactile-perception system 222
 - dynamic pseudo-memcapacitors (DPMs) 192
 - dynamic random-access memory (DRAM) 176
- e**
- EDL transistors (EDL-Ts) 99
 - EGT based neuromorphic transistors 103–105
 - electrical-double-layer (EDL) modulation 99

- electrically programmable read-only memory (EPROM) 126
- electrochemical doping/de-doping 99
- electrochemical metallization cells (ECM) 8
- electrochemical metallization memristors (ECMMs) 93
- electrochemical random-access memory (ECRAM) 176
- electrochemical transistors (ECTs) 99
- electro-iono-photoactive 2D chalcogenide neuristors 113
- electrolyte-gate transistors (EGTs) 99, 158–162
- electron energy-loss spectra (EELS) 15, 16
- electronic artificial neurons and synapses 125
- ethyl viologen diperchlorate [EV(ClO₄)₂]/triphenylamine-containing polymer 152
- excitatory postsynaptic current (EPSC) 20
- excitatory postsynaptic potential (ePSP) 18
- f**
- fault-tolerant algorithms 186
- ferroelectric devices 125
- ferroelectric field-effect transistors (FeFETs) 162–163, 176
- ferromagnetic (FM) layers 48
- field-induced nucleation model 128
- filamentary-type resistive switching 8–14
- anion migration related filaments 11–14
- cation migration related filaments 8–11
- flash memory 176
- flexible floating-gate synaptic transistor 158
- flexible gate-tunable resistive switching 190
- flexible memristors 95
- flexible oxide-based neuromorphic transistor 103
- floating-gate transistors 157–159
- free layer (FL) 48
- fully-connected networks (FCNs) 173
- g**
- gate coupling effects 98
- Ge₁Sb₂Te₄ 127
- Ge₁Sb₄Te₇ 127
- Ge₂Sb₂Te₅ 127, 129
- Ge₃Sb₂Te₆ 127
- Ge₈Sb₂Te₁₁ 127
- Ge₁₀Si₁₂As₃₀Te₄₈ 126
- GeTe-Sb₂Te₃ pseudo-binary alloy system 126, 127
- GeTe/Sb₂Te₃ superlattice-like layers 130
- graphene 3
- graphene quantum dots (GQDs)/organic hybrid systems 156
- graphics processing units (GPUs) 174
- h**
- halide perovskites 150, 154, 155
- haptic type (mechano)neuron 223
- hardware neural networks 139–143
- heavy mental (HM) 57
- Hebb's rule 188
- heterosynaptic depression 98
- heterosynaptic facilitation 98
- heterosynaptic plasticity 97–98, 188
- HH neurons 29, 34
- highly interconnected neuromorphic architecture (HINA) 161
- high resistance state (HRS) 4, 8, 48, 56, 58, 93, 126, 185
- high-resolution transmission electron microscopy (HRTEM) 12, 33
- Hodgkin–Huxley (HH)
- axon 35
- model 28, 29
- neuron model 188
- homosynaptic plasticity 96, 98
- Hopfield neural network (HNN) 139, 203–204

human senses 218
 hyperdimensional (HD) computing 196,
 201

i

IBM's TrueNorth 176
i-carrageenan 150
 iconic neuron 223
 Ielmini model 129
 IF neurons 29
 indium–zinc–oxide (IZO) 20, 100
 inhibited postsynaptic current
 (IPSC) 20
 inhibitory postsynaptic potential
 (IPSP) 18
 injection locking 73
 inorganic halide perovskite quantum dots
 (IHP QDs) 165
 in-plane magnetic anisotropy (IMA) 48
 integrate-fire (IF) model 28, 56
 intelligent tasks 204, 220, 223–226
 Intel's Loihi 176
 interface-type resistive switching
 n-type semiconductor 15
 spectromicroscopy 16
 TEM and EELS 16
 Internet of Things (IoT) 18
 ion coupling 99
 ion gel-gated field-effect transistors
 222
 ionic/electronic hybrid electrolyte gated
 transistors (EGTs) 99
 ion migration-based memristors
 153–155
 ion-sensitive field-effect transistors 102
 ions mobility 10–11
 IZO-based EDL transistor 103

k

1Kb HfO_x-based 1T1R artificial synapse
 array 202
 160Kb 1T1R memristor array 181
 64k-cell PCM synaptic array 142
 Kirchhoff laws 7

l

Landau-Lifshitz-Gilbert (LLG) equation
 54
 4-layer Bayesian neural network 181
 4-layer three-dimensional (3D) vertical
 RRAM (VRAM)/FinFET kernel
 196
 leaky-integrate-and-fire (LIF) 28, 29, 31,
 32, 36, 54, 65, 188
 Li_xMoS₂-based synaptic device 97
 local graded potential (LGP) 28
 locally competitive algorithm (LCA) 38
 logic-in-memory circuits 196
 long-short term network (LSTM) 139
 long term depression (LTD) 23, 131
 long-term memristive synapses 23–27
 long-term plasticity (LTP) 18, 19
 long term potentiation (LTP) 23, 24, 131
 long-term potentiation/depression
 (LTP/LTD) 98, 188
 low resistance state (LRS) 8, 48, 58, 93,
 126
 low resistive state (LRS) 4, 151
 low-voltage indium-zinc-oxide
 homojunction
 electric-double-layer transistor
 102

m

magnetic devices 125
 magnetic random-access memory
 (MRAM) 176
 magnetic skyrmions 62, 64
 magnetic tunnel junction (MTJ)
 all-spin artificial neural network
 61–62
 all-spin spiking neural network 62
 analog-like synaptic device 52–54
 artificial neural device 57–61
 spiking neural device 54–57
 stochastic binary synaptic device
 51–52
 write/read operation
 binary magnetic tunnel junction
 48–49

- multi-level spintronic memristor 49–51
 - Manhattan rule 38
 - matrix-vector multiplications (MVMs) 176
 - mechanoreceptors 218
 - membrane potential (MP) 27, 28, 31, 54, 105, 137, 218
 - memristive bioinspired devices 17
 - memristive neurons 27–36
 - memristive synapses 18–27
 - memristive device 1, 8
 - materials 2–4
 - metal/insulator/metal structure 1–2
 - memristive neural networks
 - ANN computing 36–39
 - SNN computing 39–41
 - memristive neurons 27–36
 - biophysical memristive neurons 34–36
 - bioplausible memristive neurons 31–34
 - memristive synapses 18–27
 - long-term memristive synapses 23–27
 - short-term memristive synapses 20–23
 - memristor-based CIM macros 183
 - memristor based neuromorphic devices 92–96
 - memristors 125
 - metal filament conducting-based memristors 150–152
 - metal/insulator/metal (MIM) 1–2
 - metaplasticity 92
 - metavalent bonding 129
 - mimicked multi-store memory model 94
 - MIT cell 34
 - Modified National Institute of Standards and technology (MNIST) 37
 - monolayer molybdenum disulfide (MoS_2) 98
 - Moore's law 91
 - multi-gate neuromorphic transistor 105–106
 - multi-gate neuromorphic transistor for pH-sens 103
 - multi-gate P3HT electrochemical transistors (ECTs) 109
 - multi-gate synergic modulation 105
 - multilayer perceptron (MLP) 125, 139
 - multi-level spintronic memristor 49–51
 - multi-memristive synapse design 190
 - multiple $\text{Au}/\text{Li}_x\text{MoS}_2/\text{Au}$ memristors 97
 - multiplication-addition-permutation (MAP) 196
 - multi-terminal memtransistor 98, 190
 - multi-terminal neuromorphic memristors
 - heterosynaptic plasticity 97–98
 - memristor based neuromorphic devices 92–96
 - multi-terminal memtransistor 98
 - synaptic competition and cooperation 96–97
 - multi-terminal neuromorphic transistors
 - artificial auditory device 113–114
 - artificial tactile device 109–112
 - artificial vision device 112–113
 - chemical-biosensors 101–102
 - dendrite neuron and dendritic algorithm 106–109
 - EGT based neuromorphic transistors 103–105
 - multi-gate neuromorphic transistor 105–106
 - multi-gate neuromorphic transistor for pH-sens 103
 - neuron MOS (νMOS) transistor 99
 - neuron transistors for
 - chemical-biosensor 102
 - pattern recognition 109
 - multi-terminal synaptic transistor structure 115
- n**
- Na^+ channels 27
 - nanogranular SiO_2 based electrolyte 102
 - nanogranular SiO_2 electrolyte film 103
 - nanogranular SiO_2 films 100

- nanoparticle organic memory field-effect transistors (NOMFET) 158
- Nb_2O_5 -based Mott devices 192
- NbO_x -based Mott memristors 202
- neural networks 54
- neuromorphic computing 2
 - background introduction 173–174
 - based synchronization 77
 - CMOS-based 174–176
 - dendritic computing 196–202
 - DNNs based on synaptic devices 178–187
 - Hopfield neural network (HNN) 203–204
 - hyperdimensional (HD) computing 196, 201
 - motivation for 174
 - oscillatory neural networks (ONNs) 203
 - principles of memristors 176–177
 - reservoir computing 202–203
 - SNNs based on neuromorphic devices 187–195
- neuromorphic perceptual systems 227
 - artificial perception 219–221
 - challenges and perspectives 228–229
 - sensation and perception 218–219
- neuromorphic tactile processing system (NeuTap) 110
- neuron MOS (ν MOS) transistor 99
- neuron transistors for chemical-biosensor 102
- nociceptive memory 223
- nociceptors 218
- nonvolatile resistive switching 4, 7, 8, 31
- normal sensor 221
- n-type semiconductor 15
- nucleation-dominant $\text{GeTe-Sb}_2\text{Te}_3$ pseudo-binary alloy system 127
- O**
- Ohm and Kirchhoff laws 7, 18
- olfactory memory 223
- on-chip memory (SRAM) 183
- one-selector-one-resistor (1S1R) 179
- one-transistor-one-memristive device (1T1M) 37, 41
- one-transistor-one-resistor (1T1R) 179
- optoelectronic transistors 164–165
- organic digital mechanoreceptor 222
- organic neuromorphic devices
 - artificial visualization systems 166–167
 - tactile-perception systems 167–169
 - three-terminal devices 157–165
 - two-terminal devices 149–157
- organometallic halide perovskites 154
- oscillators 72
- oscillatory neural networks (ONNs) 203
- ovonic memory switching (OMS) 126
- ovonic threshold switching (OTS) 126
- P**
- paired-pulse depression (PPD) 20, 21
- paired-pulse facilitation (PPF) 20–22, 92
- passive memristive device (0T1R) 179
- pattern recognition 109, 226
- Pavlov classical conditioning 113
- Pavlov's learning behaviors 108
- $(\text{PEA})_2\text{PbBr}_4$ 155
- PCMO 16
- 2-PCM synapse 133
- $\text{Pd/HfO}_2/\text{Ta}$ memristor arrays 192
- P-doped nanogranular SiO_2 films 100
- PEDOT+PSS electrochemical transistor 109
- PEO-EV(ClO_4)₂/triphenylamine-based polyimide (TPA-PI) system 153
- PEO-LiCF₃SO₃/poly[2-methoxy-5-(2-ethylhexyloxy)-1,4-phenylenevinylene] (MEH-PPV) system 153
- perovskite quantum dot (QD) 113
- perpendicular magnetic anisotropy (PMA) 48, 49
- persistent photoconductivity (PPC) effect 113
- phase-change heterostructure (PCH) 136
- phase-change memory (PCM) 176

- phase-change storage disc technology 126
- phase locked loop (PLL) 72
- photoemission electron microscopy (PEEM) 13
- piezoelectric nanogenerators (PENG) 110, 111, 222
- piezopotential-programmed multilevel non-volatile memory 222
- piezotronic artificial synapse 110
- pinned layer (PL) 48
- plasma-enhanced chemical vapor deposition (PECVD) 100
- plasticity-related proteins (PRPs) 96
- PMOS transistor 60
- polyacrylonitrile (PAN) film 164
- polycrystalline monolayer molybdenum disulfide (MoS_2) 190
- polydopamine-based wearable memristor device 95
- polyethylene oxide (PEO)/terpyridyl-iron polymer (TPy-Fe)/ITO structure 153
- poly (vinyl alcohol)-graphene oxide (PVA-GO) hybrid nanocomposite 95
- poly(isoindigo-co-bithiophene) [P(IID-BT)] 163
- poly(vinylidene fluoride-co-trifluoroethylene) [P(VDF-TrFE)] 162
- poly (vinylidene fluoride-trifluoroethylene) [P(VDF-TrFE)] film 162
- poly(3,4-ethylenedioxythiophene):poly-styrene sulfonate (PEDOT:PSS) 34, 150
- poly[(1-vinylpyrrolidone)-co-(2-ethyl-dimethylammonioethyl methacrylate ethyl sulfate)] [P(VP-EDMAEMAES)] 163
- postsynaptic neurons (POSTNs) 114
- post-tetanic potentiation (PTP) 19, 20
- prestructural ordering (incubation) method 130
- presynaptic neurons (PRENs) 114
- principles of memristors 176
- programmable in-memory HD computing system 196
- programmable metallization cells (PMCs) 8
- prosthetics 217
- prosthetics and robotics applications 226
- proton-conducting graphene oxide coupled neuron transistors 108
- Pt/Ag/SiO_x:Ag/Ag/Pt diffusive memristor 192
- Pt/GeSe/Pt device 137
- Pt/Ta₂O₅/TaO_x/Pt capacitor 192
- Pt/TaO_x/AlO_y/Al dynamic memristor device 202
- pulsed laser deposition (PLD) 3
- pulses trigger depression (PPD) 22
- r**
- receptor potential 218
- rectified linear unit (ReLU) 40, 139
- recurrent neural networks (RNNs) 67, 75–77, 173, 202
- redox reaction-based memristors 152–153
- reduced instruction set computing (RISC) 183
- remote supervised method (ReSuMe) 189
- reprogrammable CMOS-RRAM CIM system 183
- reprogrammable neuromorphic computing hardware 183
- reservoir computing (RC) 47, 202–203
- reservoir computing based STO 74–75
- RESET operation 4
- resistive random-access memory (RRAM) 176
- resistive switching (RS) filamentary-type 8–14 interface-type resistive switching 14–17 *I–V* characteristics 5 nonvolatile resistive switching 7 volatile resistive switching 5–7

- resistive switching (RS) behavior 92
- resistive switching devices 125
- restricted Boltzmann machine (RBM) 142
- S**
- scanning electron micrograph (SEM) 38
- scanning transmission X-ray microscopy (STXM) 13
- Schottky barrier 15
- Sc_{0.2}Sb₂Te₃ material 130
- self-organized atomic switch networks 203
- sensation and perception 218–219
- sense amplifiers (SAs) 48, 183, 185
- sense of touch 219
- sensorimotor system 166, 167, 219, 224, 226, 229
- sensory memory (SM) 94, 222
- sensory neuron 110, 167, 217, 219–223
- short-term facilitation/depression (STF/STD) 188
- short-term/long-term synaptic plasticities (STP/LTP) 92
- short-term memristive synapses 20–23
- short-term plasticity (STP) 18, 19, 23
- sign-based backpropagation (SBP) training method 186
- silicon-on-insulator (SOI) wafers 102
- SiO_xN_y:Ag diffusive memristor 190
- skyrmion-based electronics 63
- skyrmion-based neuromorphic computing overview 62–64, 71
 - skyrmion-based neuron devices 65–67
 - skyrmion-based reservoir computing 67–68
 - skyrmion-based stochastic computing 68–69
 - skyrmion-based synapse devices 64–65
- skyrmion-based neuron devices 65–67
- skyrmion-based reservoir computing 67–68
- skyrmion-based stochastic computing 68–69
- skyrmion-based synapse devices 64–65
- skyrmion-based unconventional computing 70
- skyrmion Hall effect (SkHE) 64
- skyrmionics 63, 65
- skyrmion reshuffler device 69
- SNN computing 39–41
- SNNs based on neuromorphic devices 187–195
 - learning rules and memory principles 188–189
 - synaptic devices and neuronal devices 189–192
- 30 × 10 × 10 SNN with hybrid in-situ learning 192
- (2-4) soft-/biorobotics 217
- soma 106
- spectromicroscopy 16
- spike-based training algorithms 189
- spike rate dependent plasticity (SRDP) 25, 136
- spike-timing dependent plasticity (STDP) 24, 25, 52, 92, 131, 142, 188
- spiking neural device 54–57
- spiking neural network (SNN) 51, 125, 140, 173
- spiking rate dependent plasticity (SRDP) 92
- spin-orbit torque-magnetic tunnel junction (SOT-MTJ) 56
- spin-torque nano-oscillators 203
- spin torque oscillators (STO) advantages 77
 - associative memory based injection locking 73–74
 - device 64
 - neuromorphic computing based synchronization 77
- overview 72–73
- recurrent neural network based on delayed feedback 75–77
 - reservoir computing based 74–75
- spin transfer torque (STT) effect 48
- spintronic devices 47
- spintronic memristors 51, 62

- spintronic neuromorphic devices 47
- Stanford's Neurogrid 176
- starch-based bio-polysaccharide
 electrolyte gated
 indium-gallium-zinc oxide (IGZO)
 phototransistor 112
- starch-based flexible biomemristors 95
- static random-access memory (SRAM)
 176
- stochastic binary synaptic device 51–52
- stochastic computing (SC) 64
- Street View House Numbers (SVHN)
 dataset 202
- stretchable organic nanowire synaptic
 transistor (s-ONWST) 166
- STT-MTJ 49, 51, 52
- Stuck-At-Fault (SAF) 187
- synapse 18
- synaptic cell programming 180
- synaptic filtering 92
- synaptic plasticity 188
- synaptic weight 64
- t**
- tactile-perception systems 167–169
- tactile sensation 109
- Ta/EV(ClO₄)₂ 153
- TaO_x-based bilayer memristors 190
- Te₄₈As₃₀Si₁₂Ge₁₀ chalcogenide 128
- Te₈₁Ge₁₅Sb₂S₂ 126
- tensor processing units (TPUs) 174
- Tera/Giga operations per second
 (T/GOPS) 176
- tetrafluoroethylene-perfluoro-3,6-dioxa-
 4-methyl-7-octenesulfonic acid
 copolymer (PFI) 154
- thermoreceptors 218
- three-dimensional integrated circuit
 architecture 220
- 3D XPoint™ 126
- three-terminal organic neuromorphic
 devices
 electrolyte-gate transistors (EGTs)
 158–162
- ferroelectric field-effect transistors
 (FeFETs) 162–163
- floating-gate transistors 157–158
- optoelectronic transistors 164–165
- threshold switching (TS) devices 136
- threshold switching memristor (TSM)
 191
- “Tiki-Taka” training algorithm 186
- TiO₂-based device 13
- top electrode (TE) 11
- trans-impedance amplifiers (TIAs) 179
- transition metal chalcogenides
 (TMDs) 3
- transmission electron microscopy
 (TEM) 9
- interface-type resistive switching
 14–17
- Pt/TiO₂/Pt device 12
- Ti/PCMO junction 16
- 1T1R memristor-based synapses 190
- 128 × 8 1T1R memristor array 181
- two-dimensional (2D) planar geometry
 98
- two-terminal organic neuromorphic
 devices
 charge-trapping-based memristors
 155–157
- ion migration-based memristors
 153–155
- metal filament conducting-based
 memristors 150–152
- redox reaction-based memristors
 152–153
- u**
- ultra-low-power SNN processor 142
- unconditioned stimulus (US) 108, 112,
 113
- UZH's ROLLS 176
- v**
- valence change mechanism (VCM) 11,
 93
- valence change memory memristors
 (VCMMs) 93

- vector-matrix multiplication (VMM) 7, 18, 139
- volatile resistive switching 5–7
- voltage controlled oscillators (VCOs) 72
- voltage-gated calcium (Ca^{2+}) channels 105

- W**
- wearable medical devices 217
- weighted summation 7
- Werbos's backpropagation algorithm 173

- WO_x memristors 202

- X**
- X-ray absorption spectroscopy (XAS) 13
- X-ray diffraction (XRD) 13
- X-ray PEEM (XPEEM) 14
- $30 \times 10 \times 10$ SNN with hybrid in-situ learning 192

- Z**
- ZJU's Darwin 176